AMENDMENTS TO THE CLAIMS

- 1. (Original) A resin for a photoresist composition, having a hydroxyl group bonded to a carbon atom at a polymer terminal, wherein a carbon atom in an α -position to said hydroxyl group has at least one electron attractive group.
- 2. (Original) A resin for a photoresist composition according to claim 1, having a -CR¹R²OH group at a polymer terminal, wherein R¹ and R² each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R¹ and R² is an electron attractive group selected from a group consisting of halogen atoms and halogenated alkyl groups.
- 3. **(Original)** A resin for a photoresist composition according to claim 1, wherein said electron attractive group is a fluorine atom or a fluorinated alkyl group.
- 4. (Original) A resin for a photoresist composition according to claim 2, wherein a proportion of structural units (M1) comprising said -CR¹R²OH group is at least 1 mol%, relative to a combined 100 mol% of all structural units other than said structural units (M1) within said resin for a photoresist composition.
- 5. (Original) A resin for a photoresist composition, having a substituent with a pKa value within a range from 6 to 12 at a polymer terminal.

- 6. (Original) A resin for a photoresist composition according to claim 5, wherein said substituent is a -CR¹R²OH group, wherein R¹ and R² each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R¹ and R² is an electron attractive group selected from a group consisting of halogen atoms and halogenated alkyl groups.
- 7. (Currently amended) A resin for a photoresist composition according to claim 1 or 5, further comprising an acid dissociable, dissolution inhibiting group.
- 8. (Original) A resin for a photoresist composition according to claim 7, further comprising (a1) a structural unit derived from a (meth)acrylate ester having an acid dissociable, dissolution inhibiting group, and (a2) a structural unit derived from a (meth)acrylate ester having a lactone ring.
- 9. (Original) A resin for a photoresist composition according to claim 8, further comprising (a3) a structural unit derived from a (meth)acrylate ester having a hydroxyl group.
- 10. (Currently amended) A resin for a photoresist composition according to claim 1 or 9, with a weight average molecular weight of no more than 12,000.
- 11. (Currently amended) A photoresist composition, comprising a resin for a photoresist composition according to claim 1 or 5.

- 12. (Original) A photoresist composition according to claim 11, further comprising an acid generator as a component (B).
- 13. (Original) A photoresist composition according to claim 12, comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.
- 14. (Original) A photoresist composition according to claim 12, comprising as said component (B), a sulfonium compound represented by either of general formulas (b-1) and (b-2) shown below:

$$R^{1}$$
 SO_{2} ... (b-1)
 R^{3} SO_{2} ... (b-1)
 R^{1} $O_{2}S-Y$
 $R^{2}-S^{+}$ N ... (b-2)
 R^{3} $O_{2}S-Z$

wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represent, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; R^1 to R^3 each represent, independently, an aryl group or an alkyl group, and at least one of R^1 to R^3 is an aryl group.

15. (Original) A photoresist composition according to claim 14, further comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.

- 16. (Original) A photoresist composition according to claim 11, further comprising a nitrogen-containing organic compound.
- 17. (Original) A method for forming a resist pattern, using a photoresist composition according to claim 11.